

74V2G14

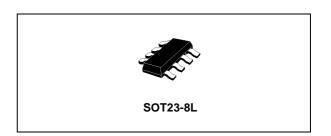
TRIPLE SCHMITT INVERTER

- HIGH SPEED: t_{PD} = 3.0ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A = 25$ °C
- TYPICAL HYSTERESIS: V_H = 800mV at V_{CC} = 4.5V V_H = 500mV at V_{CC} = 3.0V
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: $|I_{OH}| = I_{OL} = 8mA \text{ (MIN)}$ at $V_{CC} = 4.5V$ $|I_{OH}| = I_{OL} = 4mA \text{ (MIN)}$ at $V_{CC} = 3.0V$
- BALANCED PROPAGATION DELAYS: $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
 V_{CC}(OPR) = 2V to 5.5V
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74V2G14 is an advanced high-speed CMOS TRIPLE SCHMITT TRIGGER INVERTER fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS tecnology.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.



ORDER CODES

PACKAGE	T&R
SOT23-8L	74V2G14STR

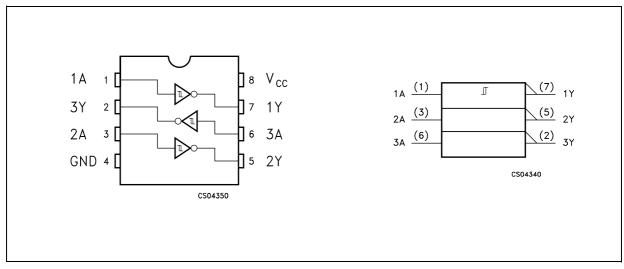
Power down protection is provided on all inputs and outputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage.

Pin configuration and function are the same as those of the 74V2G04, but 74V2G14 has hysteresis on inputs.

This device can be used to interface 5V to 3V systems and it is ideal for portable applications like personal digital assistant, camcorder and all battery-powered equipment.

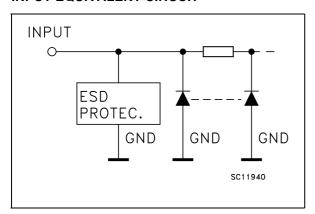
All inputs and outputs are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



June 2003 1/8

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME QND FUNCTION
1, 3, 6	1A, 2A, 3A	Data Inputs
7, 5, 2	1Y, 2Y, 3Y	Data Outputs
4	GND	Ground (0V)
8	V _{CC}	Positive Supply Voltage

TRUTH TABLE

nA	nY
L	Н
Н	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage (see note 1)	-0.5 to +7.0	V
Vo	DC Output Voltage (see note 2)	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	- 20	mA
Io	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

1) Vcc=0V
2) High or Low State

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

		Test Condition		Value							
Symbol	Parameter	V _{CC}		Т	T _A = 25°C		-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _P	High Level Input	3.0				2.20		2.20		2.20	V
	Voltage	4.5				3.15		3.15		3.15	v
		5.5				3.85		3.85		3.85	
V_N	Low Level Input	3.0		0.90			0.90		0.90		V
	Voltage	4.5		1.35			1.35		1.35		, v
		5.5		1.65			1.65		1.65		
V_{H}	Hysteresis Voltage	3.0		0.30		1.20	0.30	1.20	0.30	1.20	V
		4.5		0.40		1.40	0.40	1.40	0.40	1.40	, v
		5.5		0.50		1.60	0.50	1.60	0.50	1.60	
V_{OH}	High Level Ouput	2.0	I _O =-50 μA	1.9	2.0		1.9		1.9		
	Voltage	3.0	I _O =-50 μA	2.9	3.0		2.9		2.9		
		4.5	I _O =-50 μA	4.4	4.5		4.4		4.4		V
		3.0	I _O =-4 mA	2.58			2.48		2.4		
		4.5	I _O =-8 mA	3.94			3.8		3.7		
V _{OL}	Low Level Output	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	
	Voltage	3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =4 mA			0.36		0.44		0.55	
		4.5	I _O =8 mA			0.36		0.44		0.55	
l _l	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μΑ
I _{OPD}	Power down Output Leakage Current	0	V _O = 5.5			0.5		5		10	μА

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

		1	Test Condition		Value							
Symbol	Parameter	Parameter V _{CC} C _L		Т	T _A = 25°C -40 to 85°C -55 to 125°C					125°C	Unit	
	C	(V) (pF)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.			
t _{PLH} t _{PHL}	Propagation Delay	3.3 ^(*)	15			3.7	7.0	1.0	8.0	1.0	9.0	
	Time	3.3 ^(*)	50			5.3	8.0	1.0	9.5	1.0	10.5	nc
		5.0 ^(**)	15			3.0	5.0	1.0	6.0	1.0	7.0	ns
		5.0 ^(**)	50			4.1	6.5	1.0	7.5	1.0	8.5	

^(*) Voltage range is $3.3V \pm 0.3V$ (**) Voltage range is $5.0V \pm 0.5V$

CAPACITANCE CHARACTERISTICS

		Test Condition		Value						
Symbol	Parameter		T _A = 25°C -40 to 85°C -55 to 125		125°C	Unit				
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance			4	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)			12						pF

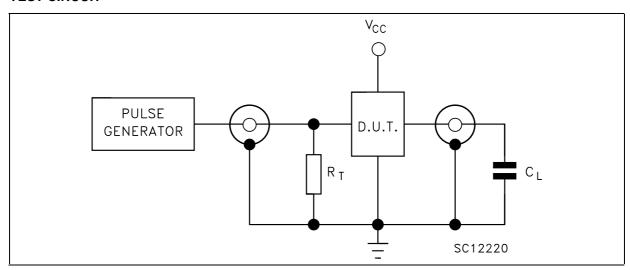
¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/3$

DYNAMIC SWITCHING CHARACTERISTICS

		Tes	st Condition	Va		
Symbol	Parameter	V _{CC} (V)		T _A = 1	25 °C	Unit
		VCC (V)		Min.	Max.	
V _{OLP}	Dynamic Low Level Quiet Out-	5.0	C _L = 50pF		0.8	V
V _{OLV}	put (note 1)	5.0	$V_{IL} = 0V, V_{IH} = 3.3V$	-0.8		\ \ \

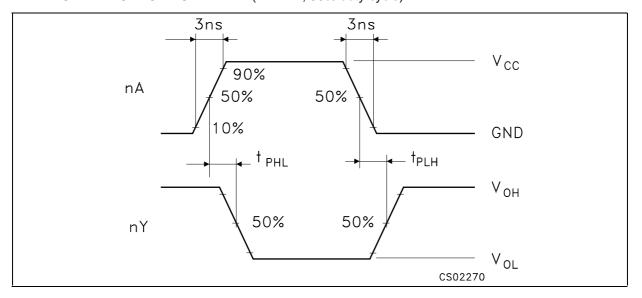
¹⁾ Number of output defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining outputs is measured in the LOW state.

TEST CIRCUIT



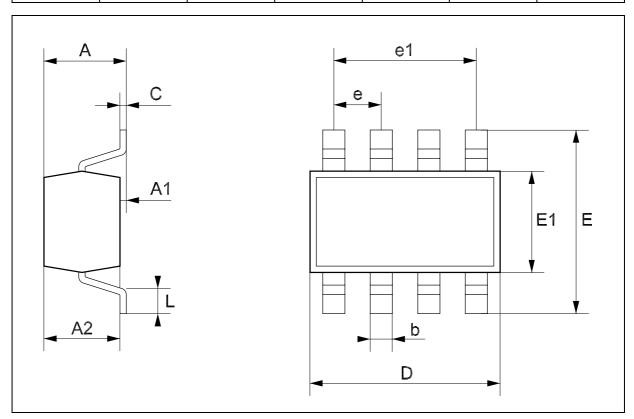
 C_L = 15/50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically $50\Omega)$

WAVEFORM: PROPAGATION DELAY (f=1MHz; 50% duty cycle)



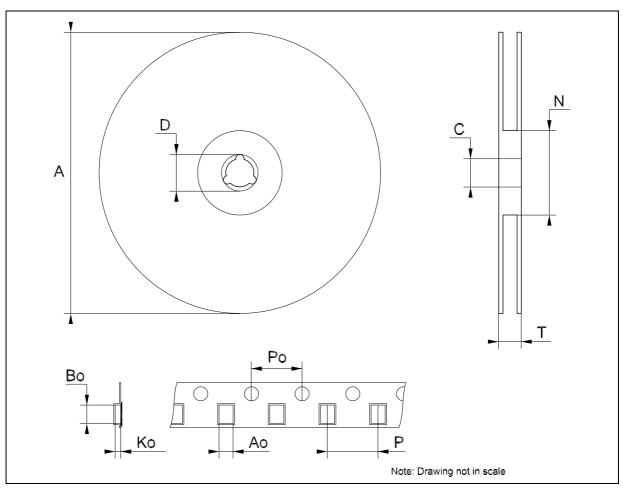
SOT23-8L MECHANICAL DATA

DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.22		0.38	8.6		14.9
С	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
е	0	.65			25.6	
e1		1.95			76.7	
L	0.35		0.55	13.7		21.6



Tape & Reel SOT23-xL MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			180			7.086		
С	12.8	13.0	13.2	0.504	0.512	0.519		
D	20.2			0.795				
N	60			2.362				
Т			14.4			0.567		
Ao	3.13	3.23	3.33	0.123	0.127	0.131		
Во	3.07	3.17	3.27	0.120	0.124	0.128		
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58		
Po	3.9	4.0	4.1	0.153	0.157	0.161		
Р	3.9	4.0	4.1	0.153	0.157	0.161		



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477

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